

*AMENDMENTS TO THE CLAIMS*

This listing of claims replaces all prior versions, and listings, of claims in the application.

1. (Canceled)

2. (Canceled)

3. (Currently Amended) ~~The A~~ semiconductor laser device ~~according to Claim 1~~ comprising:

a semiconductor body including a semiconductor substrate supporting a plurality of semiconductor layers, the semiconductor layers including an active layer in which light having a characteristic wavelength is generated, a pair of cladding layers disposed on opposite sides of the active layer, and opposed front and rear end faces transverse to the substrate and semiconductor layers, the light generated within the semiconductor laser exiting through the front end face and being reflected from the rear end face;

a film on the front end face and having a first, relatively low reflectivity at the characteristic wavelength; and

a dielectric multilayer film on the rear end face and having a second reflectivity, higher than the first reflectivity, and at least 40% at the characteristic wavelength, wherein the dielectric multilayer film includes a film of aluminum oxide in contact with the laser chip rear end face, and a film of silicon oxide, and the a film of tantalum oxide.

4. (Currently Amended) ~~The A~~ semiconductor laser device ~~according to Claim 2~~ comprising:

a semiconductor body including a semiconductor substrate supporting a plurality of semiconductor layers, the semiconductor layers including an active layer in which light having a characteristic wavelength is generated, a pair of cladding layers disposed on opposite sides of the active layer, and opposed front and rear end faces transverse to the substrate and semiconductor layers, the light generated within the semiconductor laser exiting through the front end face and being reflected from the rear end face;

a film on the front end face and having a first, relatively low reflectivity at the characteristic wavelength; and

a dielectric multilayer film on the rear end face and having a second reflectivity, higher than the first reflectivity and at least 40% at the characteristic wavelength, wherein the dielectric multilayer film is configured of a total of nine layers of has, in sequence, from the

~~side layer~~ in contact with the ~~laser chip rear end face~~, at least three paired layers, and a final film of aluminum oxide, and each of the paired layers includes an aluminum oxide film, ~~and a tantalum oxide film, an aluminum oxide film, a tantalum oxide film, an aluminum oxide film, a tantalum oxide film, an aluminum oxide film, a tantalum oxide film, and an aluminum oxide film.~~

5. (Currently Amended) The semiconductor laser device according to Claim 4, wherein the dielectric multilayer film has N layers, each of the first to ~~eightth~~ (N-1)th layers, from the ~~side layer~~ in contact with the ~~laser chip rear end face~~, has a thickness equivalent to  $\lambda/4$  in terms of optical length, ~~at an oscillation the characteristic wavelength  $\lambda$  of the laser chip~~, and the ~~ninth~~ Nth layer has a thickness equivalent to  $\lambda/2$  in terms of optical length at the characteristic wavelength.

6. (Currently Amended) The semiconductor laser device according to Claim 3, wherein the dielectric multilayer film ~~is configured of a total of eight layers of~~ has, in sequence, from the ~~side layer~~ in contact with the ~~laser chip rear end face~~, ~~an a first film of aluminum oxide film~~, at least three paired layers, and a final film of silicon oxide, and each paired layer includes a silicon oxide film, and a tantalum oxide film, ~~a silicon film, a tantalum oxide film, a silicon film, a tantalum oxide film, and a silicon film.~~

7. (Currently Amended) The semiconductor laser device according to Claim 6, wherein the dielectric multilayer film has N layers, the first layer, from the ~~side layer~~ in contact with the ~~laser chip rear end face~~, has a thickness equivalent to  $\lambda/2$  in terms of optical length, ~~at an oscillation the characteristic wavelength  $\lambda$  of the laser chip~~, and each of the second to ~~seventh~~ (N-1)th layers has a thickness equivalent to  $\lambda/4$  in terms of optical length at the characteristic wavelength, and the ~~eighth~~ Nth layer has a thickness equivalent to  $\lambda/2$  in terms of optical length at the characteristic wavelength.